PNP Silicon General Purpose Amplifier Transistor

This PNP transistor is designed for general purpose amplifier applications. This device is housed in the SOT–723 package which is designed for low power surface mount applications, where board space is at a premium.

Features

- Reduces Board Space
- High h_{FE}, 210–460 (Typical)
- Low V_{CE(sat)}, < 0.5 V
- ESD Performance: Human Body Model; > 2000 V, Machine Model; > 200 V
- Available in 4 mm, 8000 / Tape & Reel
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These are Pb–Free Devices

MAXIMUM RATINGS ($T_A = 25^{\circ}C$)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{(BR)CBO}	-60	Vdc
Collector-Emitter Voltage	V _{(BR)CEO}	-50	Vdc
Emitter-Base Voltage	V _{(BR)EBO}	-6.0	Vdc
Collector Current – Continuous	Ι _C	-100	mAdc

THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Power Dissipation (Note 1)	PD	265	mW
Junction Temperature	TJ	150	°C
Storage Temperature Range	T _{stg}	-55 ~ +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

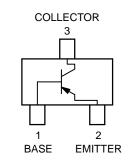
1. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.



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PNP GENERAL PURPOSE AMPLIFIER TRANSISTORS SURFACE MOUNT







F9 = Specific Device Code M = Date Code

ORDERING INFORMATION

Device	Package	Shipping [†]
2SA2029M3T5G	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSV2SA2029M3T5G	SOT-723 (Pb-Free)	8000 / Tape & Reel

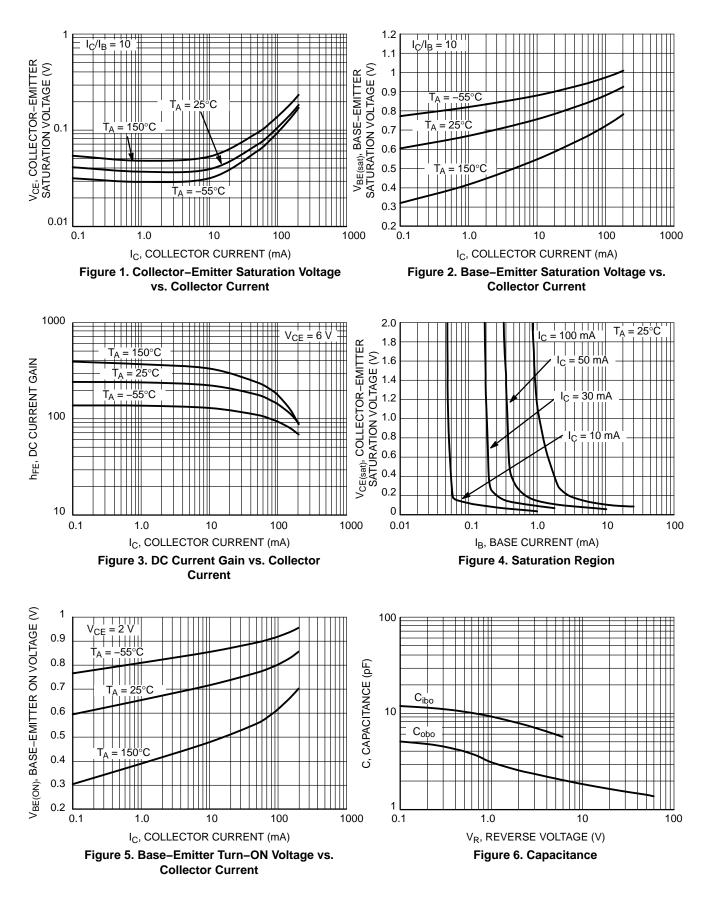
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$)

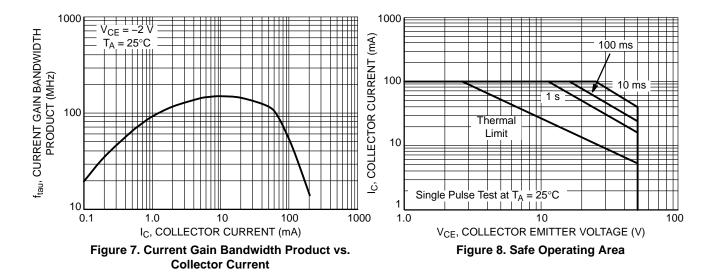
Characteristic	Symbol	Min	Тур	Max	Unit
Collector–Base Breakdown Voltage (I _C = –50 μ Adc, I _E = 0)	V _{(BR)CBO}	-60	-	-	Vdc
Collector–Emitter Breakdown Voltage ($I_C = -1.0 \text{ mAdc}, I_B = 0$)	V _{(BR)CEO}	-50	-	-	Vdc
Emitter–Base Breakdown Voltage ($I_E = -50 \ \mu Adc$, $I_E = 0$)	V _{(BR)EBO}	-6.0	-	-	Vdc
Collector–Base Cutoff Current (V _{CB} = -30 Vdc, I _E = 0)	I _{CBO}	-	-	-0.5	nA
Emitter–Base Cutoff Current ($V_{EB} = -7.0 \text{ Vdc}, I_B = 0$)	I _{EBO}	-	-	-0.1	μΑ
Collector–Emitter Saturation Voltage (Note 2) $(I_C = -50 \text{ mAdc}, I_B = -5.0 \text{ mAdc})$	V _{CE(sat)}	_	_	-0.5	Vdc
DC Current Gain (Note 2) $(V_{CE} = -6.0 \text{ Vdc}, I_C = -1.0 \text{ mAdc})$	h _{FE}	120	_	560	_
Transition Frequency ($V_{CE} = -12 \text{ Vdc}, I_C = -2.0 \text{ mAdc}, f = 30 \text{ MHz}$)	f _T	-	140	_	MHz
Output Capacitance ($V_{CB} = -12$ Vdc, $I_E = 0$ Adc, $f = 1.0$ MHz)	C _{OB}	-	3.5	-	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 2. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2%.

TYPICAL ELECTRICAL CHARACTERISTICS



TYPICAL ELECTRICAL CHARACTERISTICS



MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



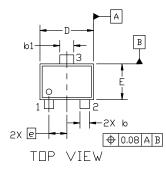
SOT-723 1.20x0.80x0.50, 0.40P CASE 631AA ISSUE E

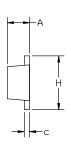
DATE 24 JAN 2024

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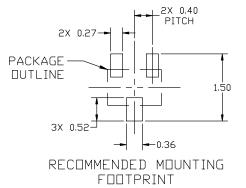
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018. CONTROLLING DIMENSION: MILLIMETERS. 1.
- 2.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH, MINIMUM З. LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



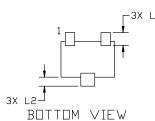


SIDE VIEW

	MILLIMETERS					
DIM	MIN.	NDM.	MAX.			
А	A 0.45		0.55			
b	0.15	0.21	0.27			
b1	0.25	0.31	0.37			
С	0.07	0.12	0.17			
D	1.15	1.20	1.25			
E	0.75	0.80	0.85			
e	0.40 BSC					
Н	1.15	1.20	1.25			
L	0.29 REF					
L2	0.15	0.20	0.25			



*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.



GENERIC **MARKING DIAGRAM***



XX = Specific Device Code Μ = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE	STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 4: PIN 1. CATH 2. CATH 3. ANOE	ODE 2. SOURCE			
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DESCRIPTION: SOT-723 1.20x0.80x0.50, 0			0.50, 0.40F			PAGE 1	OF 1
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